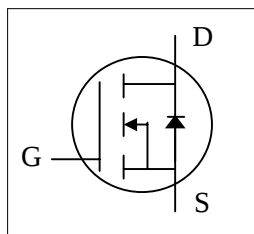




- ▼ Simple Drive Requirement
- ▼ Low Gate Charge
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant & Halogen-Free

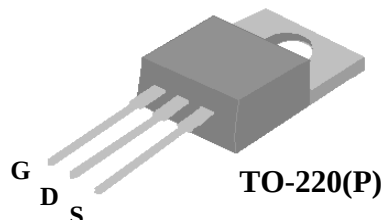
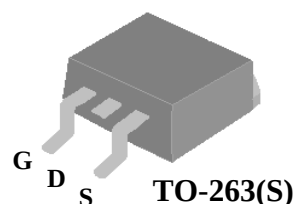


BV_{DSS}	30V
$R_{DS(ON)}$	25m Ω
I_D	28A

Description

AP40T03 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-263 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance. The through-hole version (AP40T03GP) are available for low-profile applications.



Absolute Maximum Ratings@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	+25	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	28	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, V_{GS} @ 10V	24	A
I_{DM}	Pulsed Drain Current ¹	95	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	31.25	W
	Linear Derating Factor	0.25	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	40	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	62	°C/W



AP40T03GS/P-HF

Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
ΔBV _{DSS} /ΔT _j	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I _D =1mA	-	0.032	-	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =18A	-	-	25	mΩ
		V _{GS} =4.5V, I _D =14A	-	-	45	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =18A	-	15	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =125°C)	V _{DS} =24V, V _{GS} =0V	-	-	250	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ±25V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =18A	-	8.8	-	nC
Q _{gs}	Gate-Source Charge	V _{DS} =20V	-	2.5	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	5.8	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	6	-	ns
t _r	Rise Time	I _D =18A	-	62	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	16	-	ns
t _f	Fall Time	V _{GS} =10V	-	4.4	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	655	-	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	145	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	95	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _S	Continuous Source Current (Body Diode)	V _D =V _G =0V , V _S =1.3V	-	-	28	A
I _{SM}	Pulsed Source Current (Body Diode) ¹		-	-	95	A
V _{SD}	Forward On					

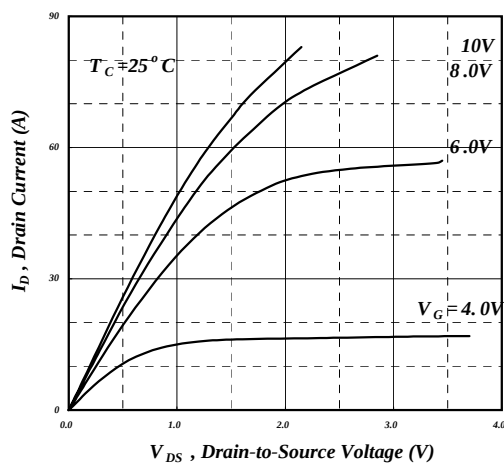


Fig 1. Typical Output Characteristics

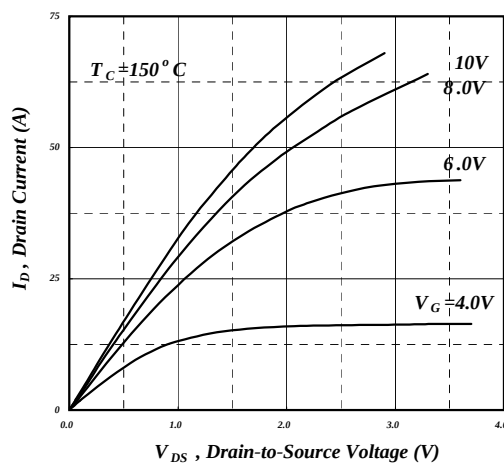


Fig 2. Typical Output Characteristics

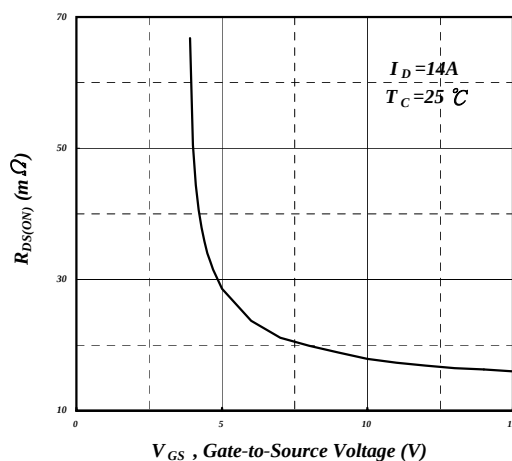


Fig 3. On-Resistance v.s. Gate Voltage

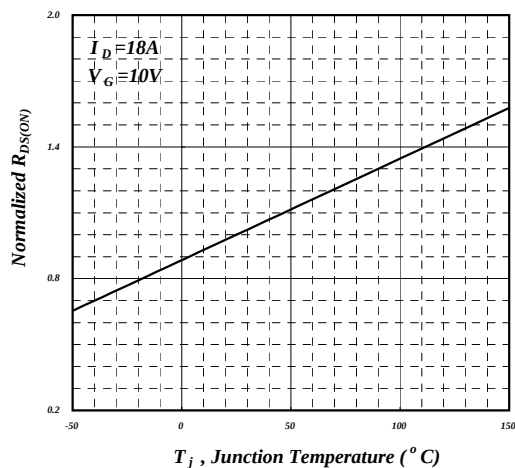


Fig 4. Normalized On-Resistance v.s. Junction Temperature

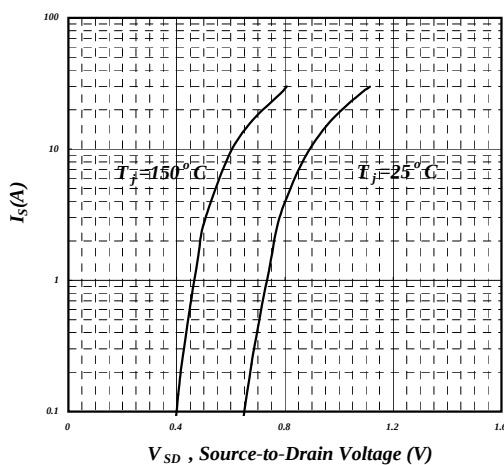


Fig 5. Forward Characteristic of Reverse Diode

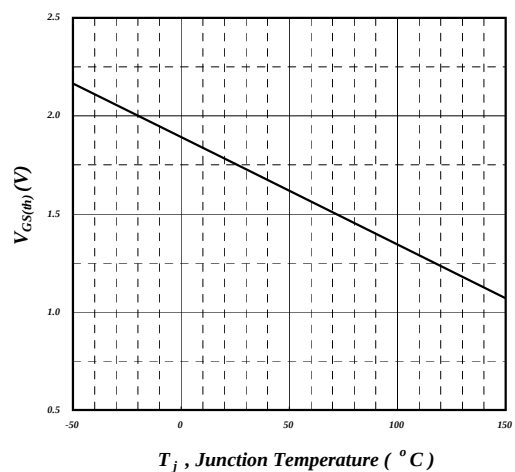


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

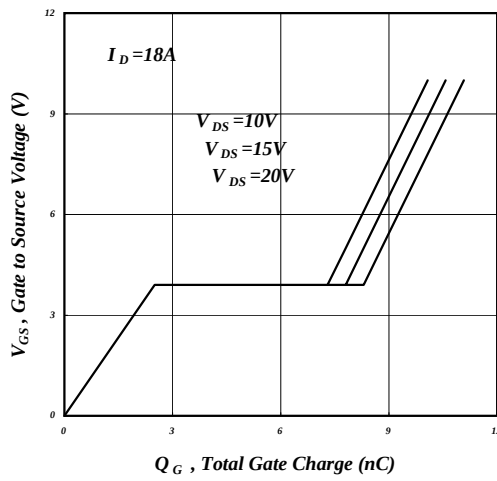


Fig 7. Gate Charge Characteristics

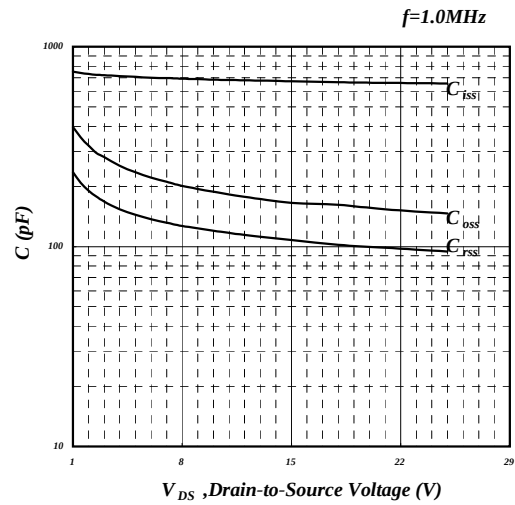


Fig 8. Typical Capacitance Characteristics

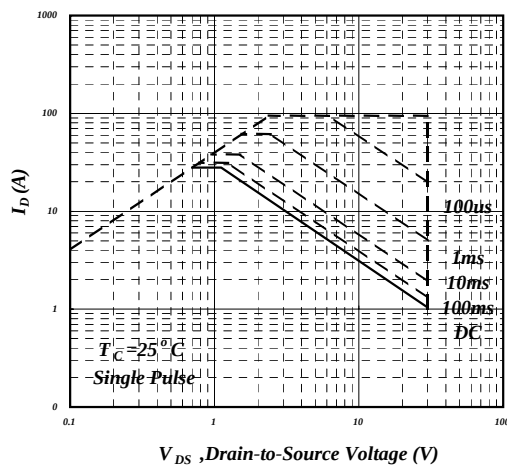


Fig 9. Maximum Safe Operating Area

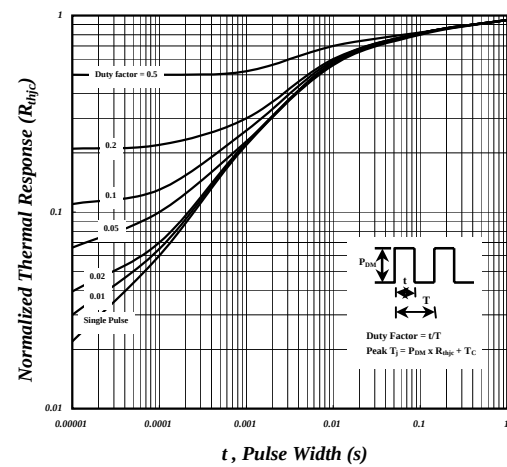


Fig 10. Effective Transient Thermal Impedance

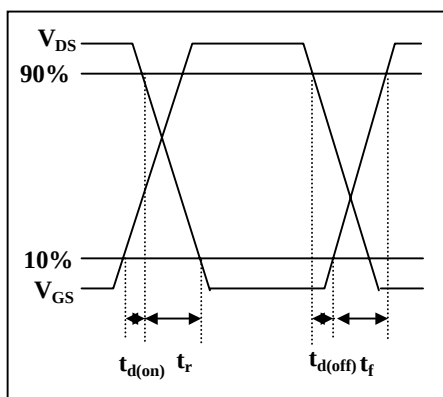


Fig 11. Switching Time Waveform

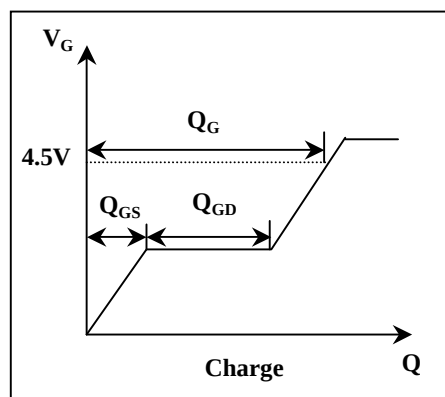
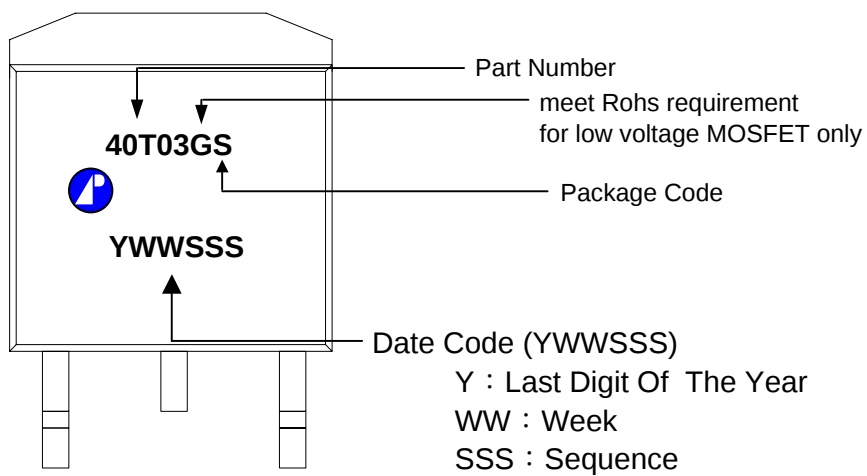


Fig 12. Gate Charge Waveform



MARKING INFORMATION

TO-263



TO-220

